

N-channel 55 V, 2.1 mOhm, 200 A continuous, logic level Application Specific MOSFET in LFPAK56E 11 July 2022

Product data sheet

1. General description

200 Amp continuous current, logic level gate drive, N-channel enhancement mode MOSFET in LFPAK56E package. Part of the ASFETs for Battery Isolation and DC Motor control family and using Nexperia's unique "SchottkyPlus" technology delivers high efficiency and low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. The ASFET is particularly suited to 36 V battery powered applications requiring strong avalanche capability, linear mode performance, use at high switching frequencies, and also safe and reliable switching at high load-current.

2. Features and benefits

- 200 A continuous current capability
- Optimised for 36 V (nominal) battery powered applications
- LFPAK56E low-stress exposed lead-frame for ultimate reliability, optimum soldering and easy solder-joint inspection
- Copper-clip and solder die attach for low package inductance and resistance, and high ID (max) rating
- Qualified to 175 °C
- Avalanche rated, 100% tested
- Low Q_G, Q_{GD} and Q_{OSS} for high efficiency, especially at higher switching frequencies
- Superfast switching with soft body-diode recovery for low-spiking and ringing, recommended for low EMI designs
- Unique "SchottkyPlus" technology for Schottky-like switching performance and low IDSS leakage
- Narrow V_{GS(th)} rating for easy paralleling and improved current sharing
- Very strong linear-mode / safe operating area characteristics for safe and reliable switching at high-current conditions

3. Applications

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- Brushless DC motor control
- Synchronous rectifier in high-power AC-to-DC applications, e.g. server power supplies
- Battery protection and Battery Management Systems (BMS)
- Load switch

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10 cell lithium-ion battery applications (36 V - 42 V)

4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	55	V	
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	200	A	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	333	W	
Tj	junction temperature			-55	-	175	°C	



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics			_		
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.63	2.1	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.83	2.4	mΩ
Dynamic ch	naracteristics			_		
Q _{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 27 V; V_{GS} = 4.5 V;	-	14	31	nC
Q _{G(tot)}	total gate charge	Fig. 12; Fig. 13	-	54	84	nC

[1] 200A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information						
Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	S	source	read			
2	S	source				
3	S	SsourceGgate		D		
4	G					
mb	D	mounting base; connected to drain	LFPAK56E; Power- SO8 (SOT1023)	G UF A mbb076 S		

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PSMN2R0-55YLH		plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch	SOT1023

7. Marking

Table 4. Marking codes				
Type number	Marking code			
PSMN2R0-55YLH	2H055L			

8. Limiting values

Table 5. Limiting values

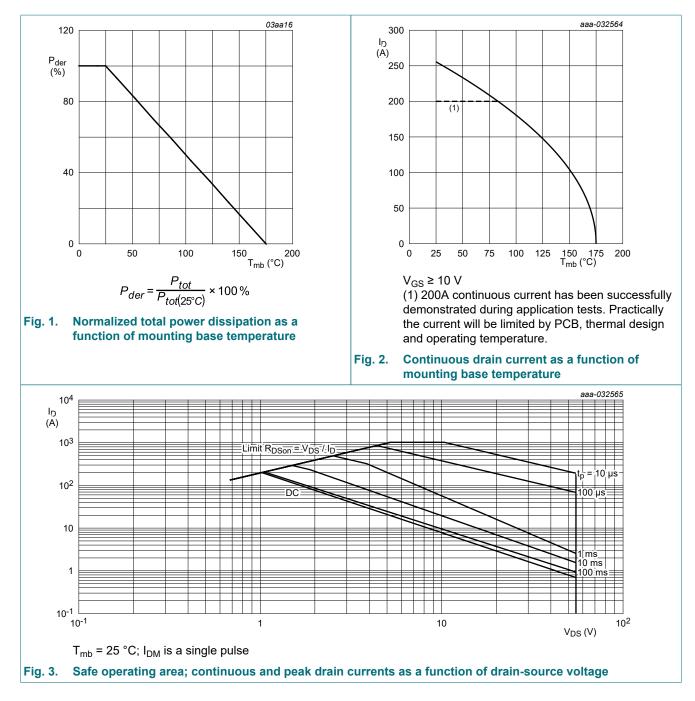
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	55	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	55	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	333	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	200	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	181	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	1049	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode	1				
ls	source current	T _{mb} = 25 °C		-	200	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1049	А
Avalanche r	uggedness	1		I		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_D = 50 \text{ A}; V_{sup} \leq \ 55 \text{ V}; R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \ ^\circ\text{C}; unclamped; \\ t_p = 417 \ \mu\text{s} \end{array} $	[2]	-	745	mJ
		$I_D = 25$ A; $V_{sup} \le 55$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped; $t_p = 1.98$ s	[2]	-	1.77	J
I _{AS}	non-repetitive avalanche current		[2]	-	115	A

[1] 200A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

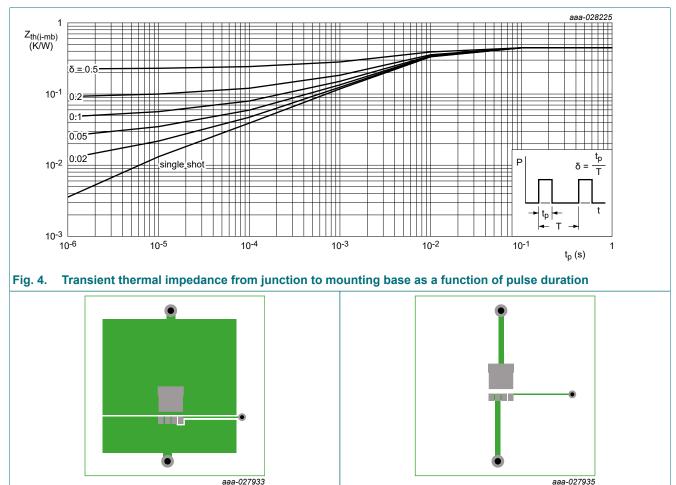
[2] Protected by 100% test

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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.33	0.45	K/W
R _{th(j-a)}		Fig. 5	-	42	-	K/W
junction to ambient	Fig. 6	-	85	-	K/W	



Copper area 25.4 mm square; 70 μm thick on FR4 board

Fig. 5. PCB layout for thermal resistance from junction to ambient

70 μm thick copper on FR4 boardFig. 6. PCB layout with minimum footprint for thermal

resistance from junction to ambient

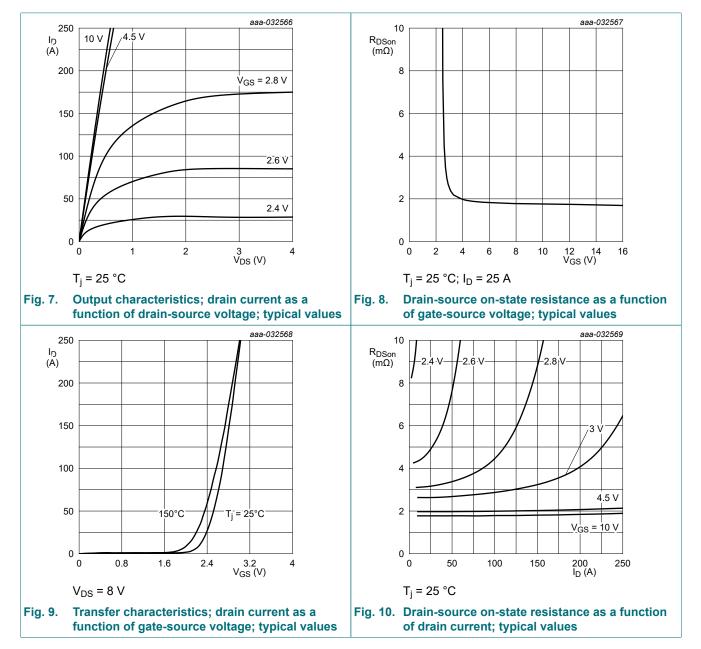
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	55	-	-	V
()	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ \text{V}; \ T_i = -55 \ ^{\circ}\text{C}$	49.5	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_{D} = 1 \text{ mA}; V_{DS} = V_{GS}; T_{j} = 25 \text{ °C}$	1.2	1.62	2.2	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.6	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 44 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μA
		V _{DS} = 44 V; V _{GS} = 0 V; T _j = 125 °C	-	3.5	-	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.63	2.1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 11	-	-	4.3	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.83	2.4	mΩ
	V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; <u>Fig. 11</u>	-	-	4.9	mΩ	
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.52	1.3	3.3	Ω
Dynamic cha	aracteristics			•		
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 27 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13	-	54	84	nC
		$I_D = 25 \text{ A}; V_{DS} = 27 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 12; Fig. 13	-	119	184	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	64	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 27 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	17	26	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	12	18	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	5.8	8.8	nC
Q _{GD}	gate-drain charge		-	14	31	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 27 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.5	-	V
C _{iss}	input capacitance	V _{DS} = 27 V; V _{GS} = 0 V; f = 1 MHz;	-	8109	11353	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	704	986	pF
C _{rss}	reverse transfer capacitance	1	-	226	542	pF
t _{d(on)}	turn-on delay time	V_{DS} = 27 V; R _L = 1.1 Ω; V _{GS} = 4.5 V;	-	39	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	38	-	ns
t _{d(off)}	turn-off delay time	1	-	60	-	ns
t _f	fall time	1	-	28	-	ns
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 27 V; f = 1 MHz; T _i = 25 °C	-	41	-	nC

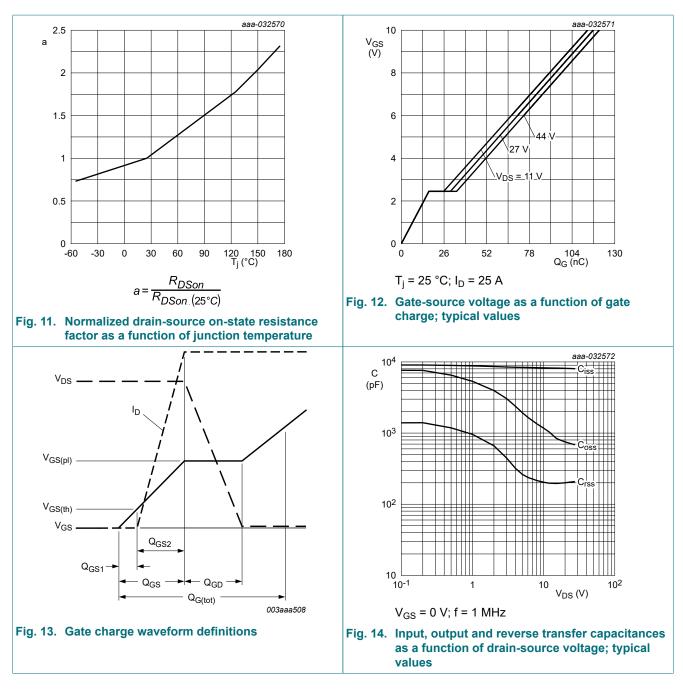
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit		
Source-drain diode									
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.75	1	V		
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 27 V; <u>Fig. 16</u> [′		-	36	-	ns		
Qr	recovered charge		[1]	-	36	-	nC		
t _a	reverse recovery rise time			-	21	-	ns		
t _b	reverse recovery fall time			-	14	-	ns		

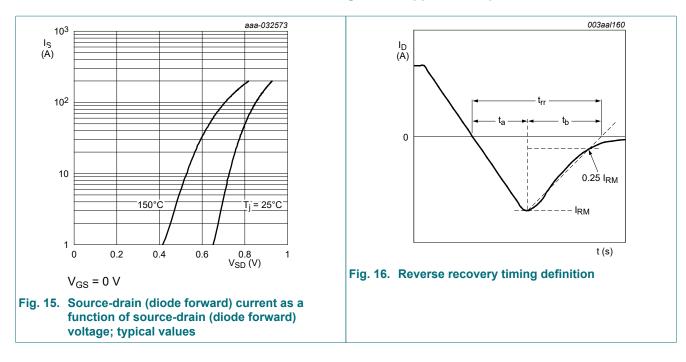
[1] includes capacitive recovery



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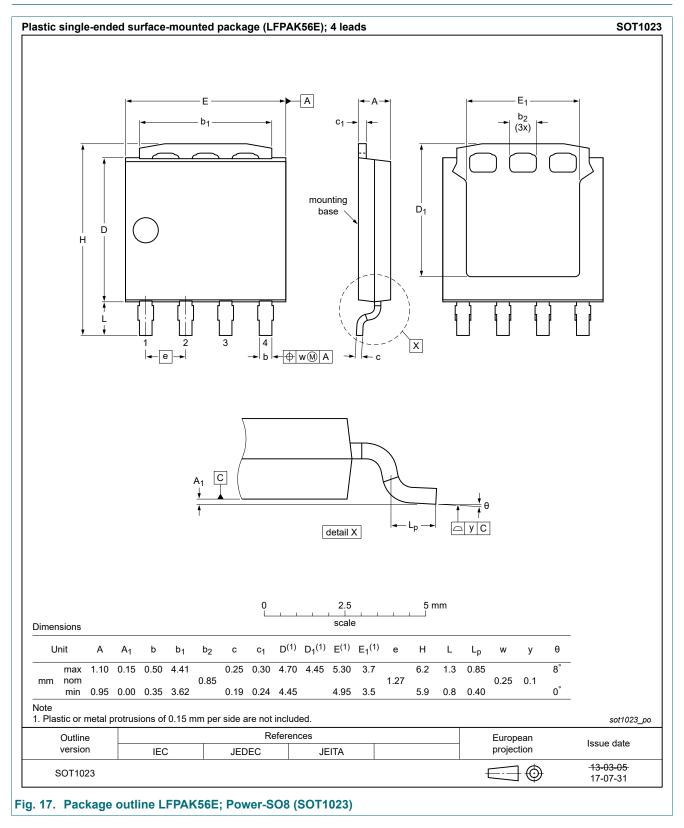


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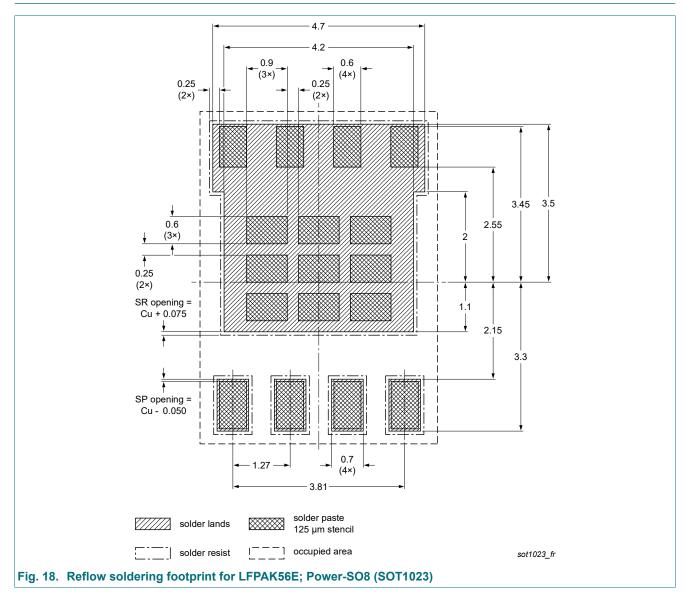


PSMN2R0-55YLH

11. Package outline



12. Soldering



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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